

2SB791(K)

Silicon PNP Epitaxial

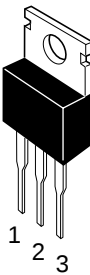
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Application

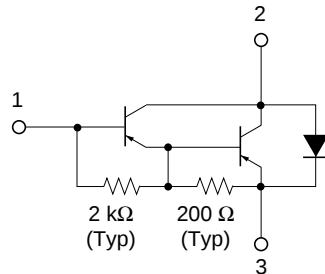
Medium speed and power switching complementary pair with 2SD970(K)

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter



Absolute Maximum Ratings (Ta = 25°C)

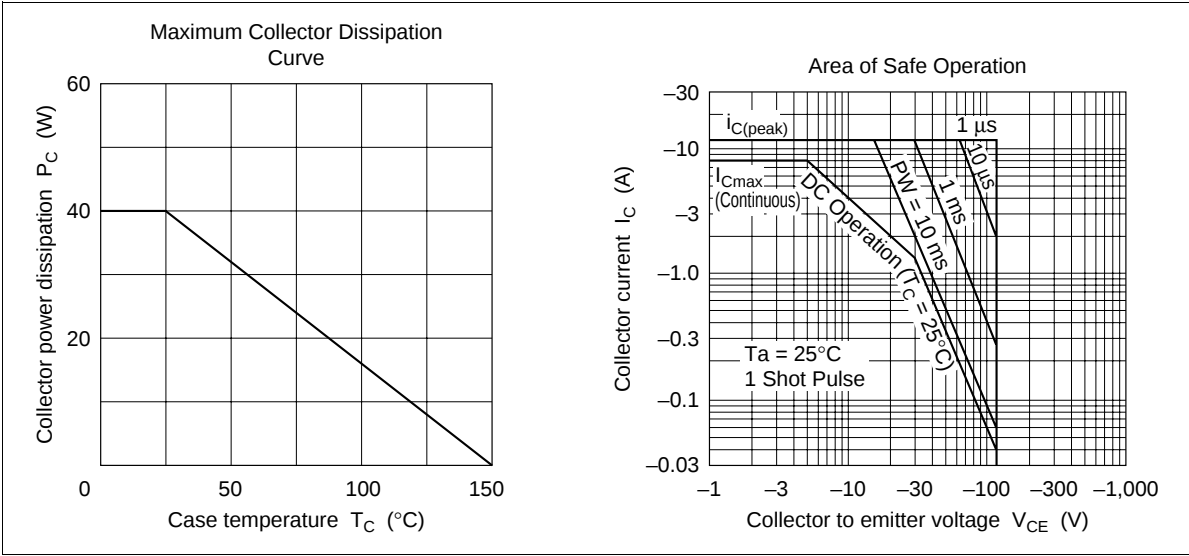
Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V_{CEO}	-120	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-8	A
Collector peak current	$I_{C(peak)}$	-12	A
Collector power dissipation	P_C^{*1}	40	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$

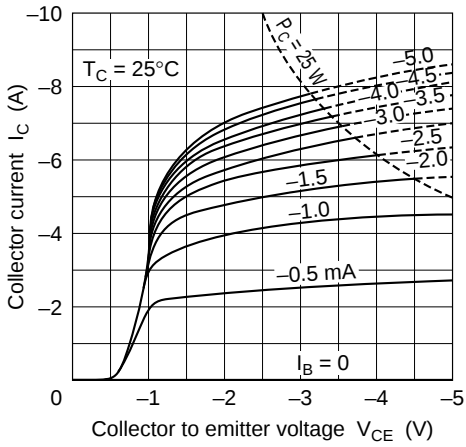
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	—	—	V	$I_C = -25\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -120\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-10	μA	$V_{CE} = -100\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3\text{ V}$, $I_C = -4\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)(1)}$	—	—	-1.5	V	$I_C = -4\text{ A}$, $I_B = -8\text{ mA}^{*1}$
	$V_{CE(sat)(2)}$	—	—	-3.0	V	$I_C = -8\text{ A}$, $I_B = -80\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)(1)}$	—	—	-2.0	V	$I_C = -4\text{ A}$, $I_B = -8\text{ mA}^{*1}$
	$V_{BE(sat)(2)}$	—	—	-3.5	V	$I_C = -8\text{ A}$, $I_B = -80\text{ mA}^{*1}$
Turn on time	t_{on}	—	0.5	—	μs	$I_C = -4\text{ A}$, $I_{B1} = I_{B2} = -8\text{ mA}$
Storage time	t_{stg}	—	1.6	—	μs	
Fall time	t_f	—	1.5	—	μs	

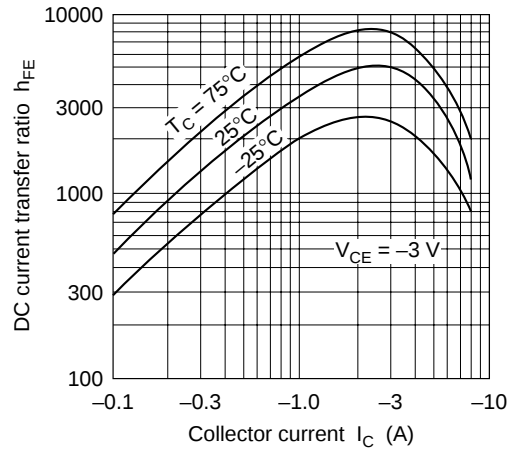
Note: 1. Pulse test



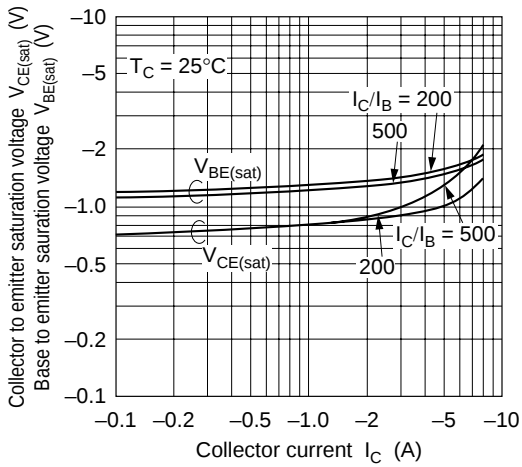
Typical Output Characteristics



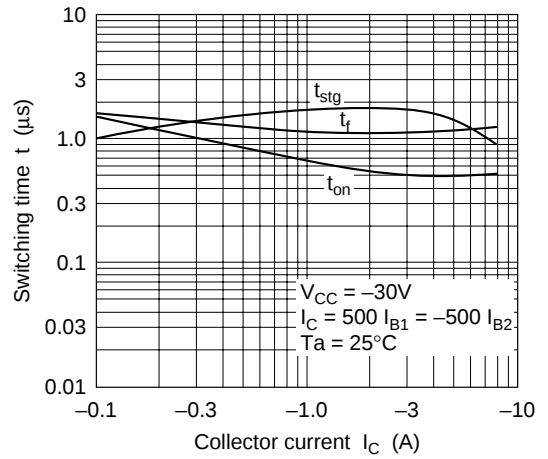
DC Current Transfer Ratio vs. Collector Current

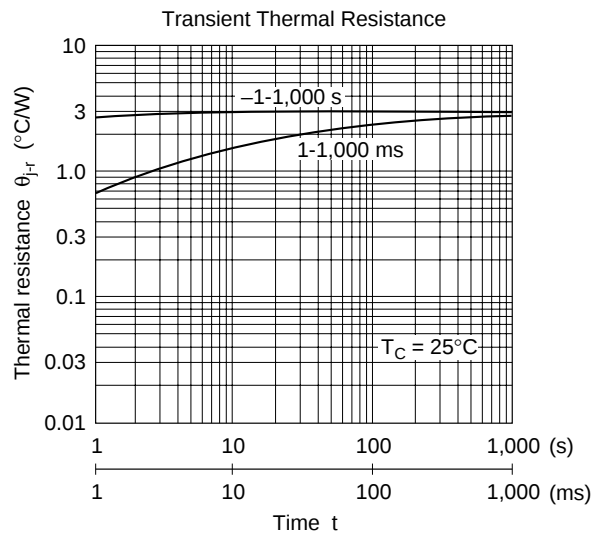


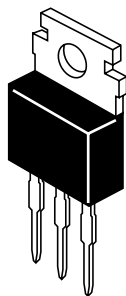
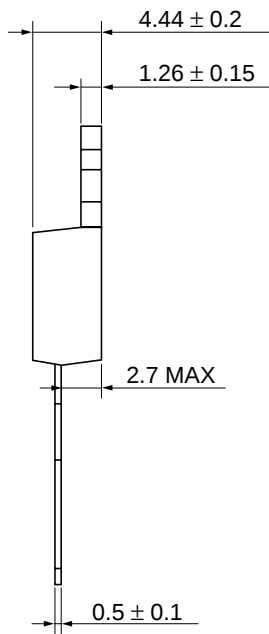
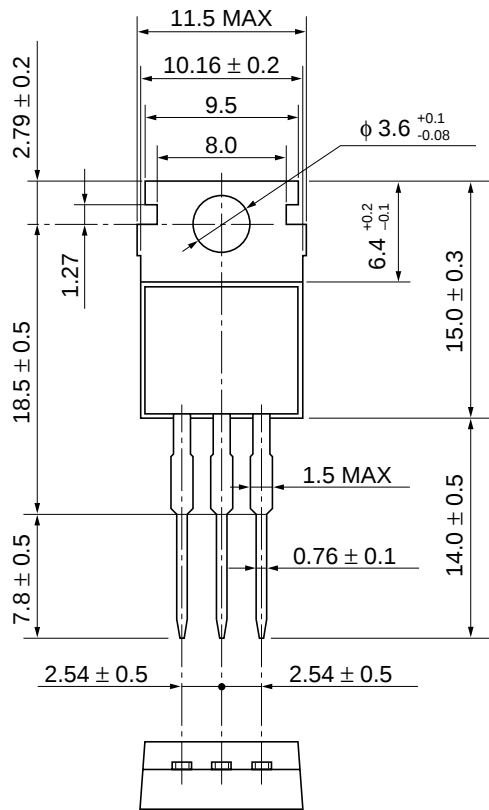
Saturation Voltage vs. Collector Current



Switching Time vs. Collector Current







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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